



DESCRIPTION

A24C08A provides 8192 bits of serial electrically erasable and programmable read-only memory (EEPROM), organized as 1024 words of 8 bits each.

The A24C08A is optimized for use in many industrial and commercial applications where low-power and low-voltage operation is essential.

The A24C08A is available in SOP8, TSSOP8, DFN8, SOT-25 and TSOT-25 packages.

AEC-Q100 Qualified is available in SOP8, TSSOP8, DFN8 and SOT-25 packages.

ORDERING INFORMATION

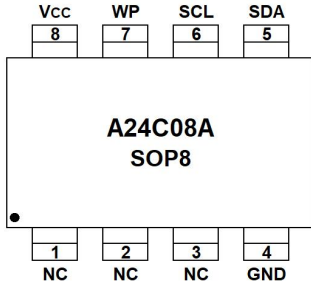
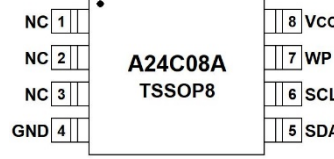

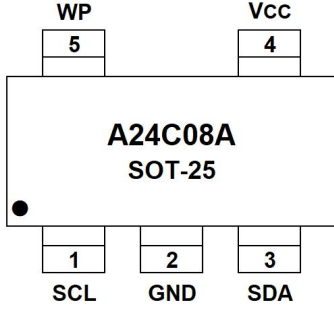
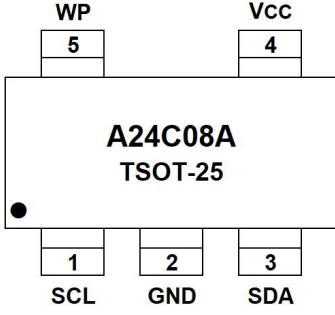
Package Type	Part Number	
SOP8 AEC-Q100 SPQ: 2,500pcs/Reel	M8	A24C08AM8VR-X
TSSOP8 AEC-Q100 SPQ: 3,000pcs/Reel	TMX8	A24C08ATMX8VR-X
DFN8 AEC-Q100 SPQ: 3,000pcs/Reel	J8	A24C08AJ8VR-X
SOT-25 AEC-Q100 SPQ: 3,000pcs/Reel	E5	A24C08AE5VR-X
TSOT-25 SPQ: 3,000pcs/Reel	TE5	A24C08ATE5VR-X
Note	X: Temperature, AEC-Q B : -40°C to +105°C C : -40°C to +125°C Q : AEC-Q100 V: Halogen Free Package R: Tape & Reel	
AiT provides all RoHS products		

FEATURES

- Compatible with all I²C bidirectional data transfer protocol
- Memory Array:
8K bits (1024X 8) of EEPROM
Page size: 16 bytes
- Extended Temperature Range
B : -40°C to +105°C
C : -40°C to +125°C
Q : -40°C to +125°C (AEC-Q100 Certificated)
- Single Supply Voltage and High Speed:
1MHz
Random and sequential Read modes
- Write:
Byte Write within 3 ms
Page Write within 3 ms
Partial Page Writes Allowed
- Write Protect Pin for Hardware Data Protection
- Schmitt Trigger, Filtered Inputs for Noise Suppression
- High-Reliability
Endurance: 4 Million Write Cycles
Data Retention: 100 Years
- Enhanced ESD/Latch-up Protection
HBM 8000V



PIN DESCRIPTION

 <p>A24C08A SOP8</p> <p>SOP8, M8 Top View</p>		 <p>A24C08A TSSOP8</p> <p>TSSOP8, TMX8 Top View</p>		 <p>A24C08A DFN8</p> <p>DFN8, J8 Top View</p>	
 <p>A24C08A SOT-25</p> <p>SOT-25, E5 Top View</p>			 <p>A24C08A TSOT-25</p> <p>TSOT-25, TE5 Top View</p>		
Pin #		Symbol	Type	Functions	
SOP8 / TSSOP8 DFN8	SOT-25 TSOT-25				
1,2,3	-	NC	-	NC	
4	2	GND	P	Ground	
5	3	SDA	I/O	Serial Data	
6	1	SCL	I	Serial Clock Input	
7	5	WP	I	Write Protect	
8	4	Vcc	P	Power Supply	

**ABSOLUTE MAXIMUM RATINGS**

DC Supply Voltage	-0.3V ~ +6.5V
Input / Output Voltage	GND-0.3V ~ V _{CC} +0.3V
Storage Temperature	-65°C ~ +150°C
Electrostatic Pulse (Human Body Model)	8000V

Stresses above may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the Electrical Characteristics is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

PIN CAPACITANCE

Applicable over recommended operating range from: T_A = 25°C, f = 1.0MHz, V_{CC} = +2.5V

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input/ Output Capacitance (SDA)	C _{I/O}	V _{I/O} =0V	-	-	8	pF
Input Capacitance (A0, A1, A2, SCL)	C _{IN}	V _{IN} =0V	-	-	6	pF

DC ELECTRICAL CHARACTERISTICS

Applicable over recommended operating range, unless otherwise noted

A24C08A-B	T _A = -40°C to +105°C	V _{CC} = +1.7V to +5.5V@400kHz V _{CC} = +2.5V to +5.5V@1MHz C _L =100 pF
A24C08A-C	T _A = -40°C to +125°C	
A24C08A-Q	T _A = -40°C to +125°C	

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Supply Current V _{CC} = 5.0V	I _{CCR}	Read at 400kHz	-	0.14	0.3	mA
Supply Current V _{CC} = 5.0V	I _{CCW}	Write at 400kHz	-	0.28	0.5	mA
Supply Current V _{CC} = 5.0V	I _{SB}	V _{IN} = V _{CC} or GND	-	0.03	2.0	μA
Input Leakage Current	I _{LI}	V _{IN} = V _{CC} or GND	-	0.10	1.0	μA
Output Leakage Current	I _{LO}	V _{OUT} = V _{CC} or V _{SS}	-	0.05	1.0	μA
Input Low Level	V _{IL}	V _{CC} = 1.7V to 5.5V	-0.3	-	V _{CC} x 0.3	V
Input High Level	V _{IH}	V _{CC} = 1.7V to 5.5V	V _{CC} x 0.7	-	V _{CC} + 0.3	V
Output Low Level V _{CC} = 1.7V	V _{OL1}	I _{OL} = 0.15mA	-	-	0.2	V
Output Low Level V _{CC} = 5.0V	V _{OL2}	I _{OL} = 3.0mA	-	-	0.4	V



AC ELECTRICAL CHARACTERISTICS (2)

Applicable over recommended operating range, unless otherwise noted

A24C08A-B	T _A = -40°C to +105°C	V _{CC} = +1.7V to +5.5V@400kHz
A24C08A-C	T _A = -40°C to +125°C	
A24C08A-Q	T _A = -40°C to +125°C	V _{CC} = +2.5V to +5.5V@1MHz
		C _L = 100 pF

Parameter	Symbol	1.7V ≤ V _{CC} < 2.5V			2.5V ≤ V _{CC} < 5.5V			Unit
		Min.	Typ.	Max.	Min.	Typ.	Max.	
Clock Frequency, SCL	f _{SCL}	-	-	400	-	-	1000	kHz
Clock Pulse Width Low	t _{LOW}	1.3	-	-	0.5	-	-	µs
Clock Pulse Width High	t _{HIGH}	0.6	-	-	0.26	-	-	µs
Noise Suppression Time	t _i	-	-	50	-	-	50	ns
Clock Low to Data Out Valid	t _{AA}	-	-	0.9	-	-	0.45	µs
Time the bus must be free before a new transmission can start	t _{BUF}	1.3	-	-	0.5	-	-	µs
Start Hold Time	t _{HD,STA}	0.6	-	-	0.25	-	-	µs
Start Setup Time	t _{SU,STA}	0.6	-	-	0.25	-	-	µs
Data In Hold Time	t _{HD,DAT}	0	-	-	0	-	-	µs
Data In Setup Time	t _{SU,DAT}	100	-	-	100	-	-	ns
Inputs Rise Time (1)	t _R	-	-	0.3	-	-	0.12	µs
Inputs Fall Time (1)	t _F	-	-	0.3	-	-	0.12	µs
Stop Setup Time	t _{SU,STO}	0.6	-	-	0.25	-	-	µs
Data Out Hold Time	t _{DH}	50	-	-	50	-	-	ns
Write Cycle Time	t _{WR}	-	1.9	3	-	1.9	3	ms
5.0V, 25°C, Byte Mode (1)	Endurance	1M	-	-	1M	-	-	Write Cycles

(1): This parameter is characterized and is not 100% tested.

(2): AC measurement conditions: R_L (connects to V_{CC}): 1.3K

Input pulse voltages: 0.3 V_{CC} to 0.7V_{CC}

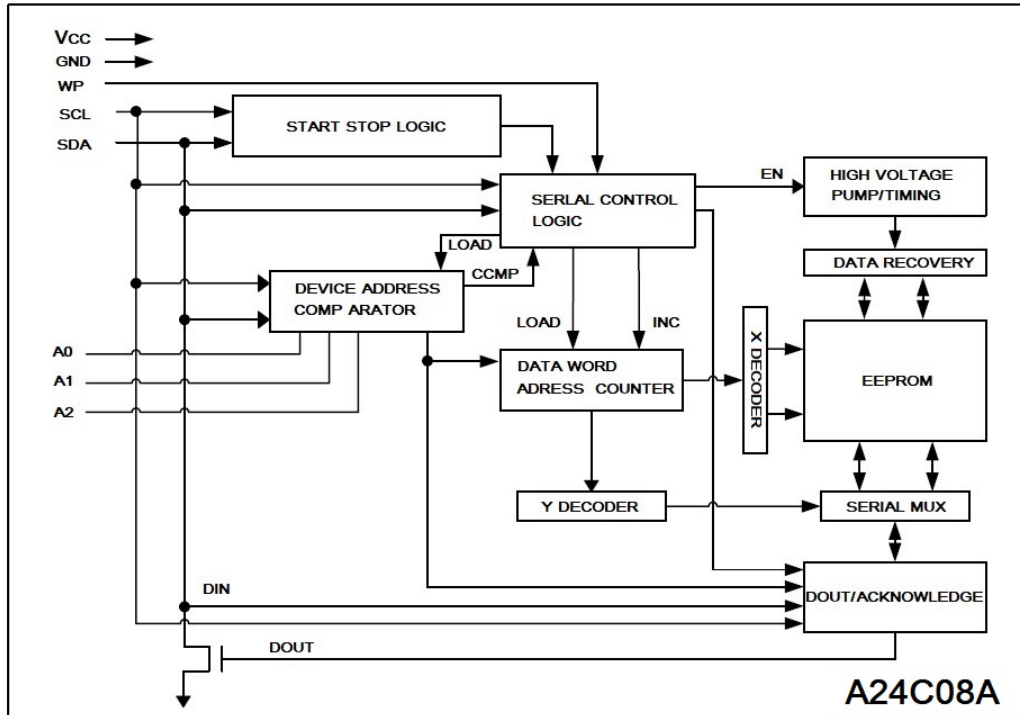
Input rise and fall time: 50ns

Input and output timing reference voltages: 0.5V_{CC}

The value of R_L should be concerned according to the actual loading on the user's system.



BLOCK DIAGRAM



DETAILED INFORMATION

SERIAL DATA (SDA): The SDA pin is bi-directional for serial data transfer. This pin is open-drain driven and may be wire-OR 'ed with any number of other open-drain or open- collector devices.

SERIAL CLOCK (SCL): The SCL input is used to positive edge clock data into each EEPROM device and negative edge clock data out of each device.

WRITE PROTECT (WP): The A24C08A has a Write Protect pin that provides hardware data protection. The Write Protect pin allows normal read/write operations when connected to ground (GND). When the Write Protection pin is connected to V_{CC}, the write protection feature is enabled and operates as shown in the following Table 1.

Table1: Write Protect

WP Pin Status	A24C08A
At V _{CC}	Full (8K) Array
At GND	Normal Read/Write Operations



FUNCTION DESCRIPTION

1. Memory Organization

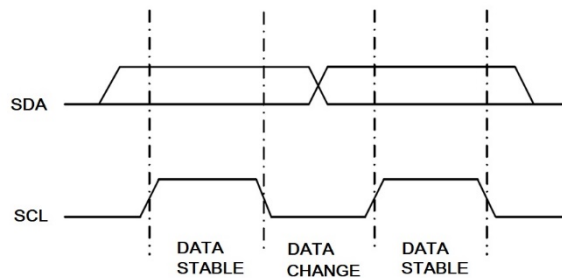
A24C08A, 8K SERIAL EEPROM: Internally organized with 64 pages of 16 bytes each, the 8K requires an 10-bit data word address for random word addressing.

2. Device Operation

CLOCK and DATA TRANSITIONS:

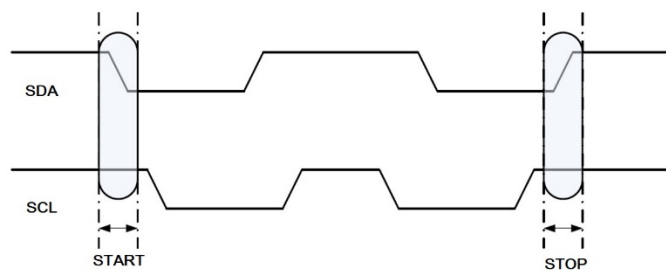
The SDA pin is normally pulled high with an external device. Data on the SDA pin may change only during SCL low time periods (see Figure 1). Data changes during SCL high periods will indicate a start or stop condition as defined.

Figure 1 Data Validity



START CONDITION: A high-to-low transition of SDA with SCL high is a start condition which must precede any other command (see Figure 2).

Figure 2 Start and Stop Definition

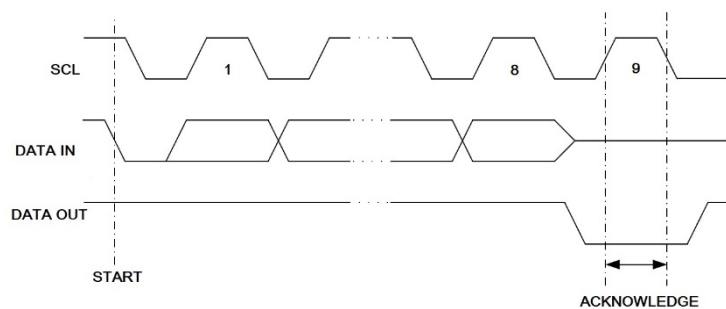


STOP CONDITION: A low-to-high transition of SDA with SCL high is a stop condition. After a read sequence, the stop command will place the EEPROM in a standby power mode (see Figure 2).

ACKNOWLEDGE:

All addresses and data words are serially transmitted to and from the EEPROM in 8-bit words. The EEPROM sends a "0" to acknowledge that it has received each word. This happens during the ninth clock cycle.

Figure 3 Output Acknowledge





STANDBY MODE: The A24C08A features a low-power standby mode which is enabled:

- (a) Upon power-up
- (b) After the receipt of the STOP bit and the completion of any internal operations.

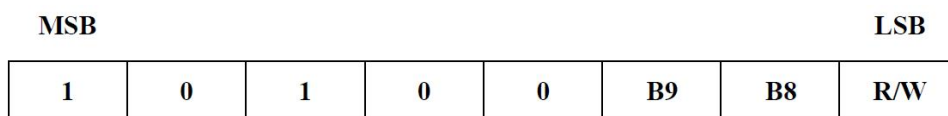
MEMORY RESET: After the protocol is interrupted, power loss or system reset, any two-wire part can be reset by following these steps:

1. Clock up to 9 cycles.
2. Look for SDA high in each cycle while SCL is high.
3. Create a start condition and a stop condition.

3. Device Addressing

The 8K EEPROM devices all require an 8-bit device address word following a start condition to enable the chip for a read or write operation (see Figure 4).

Figure 4 Device Address



The device address word consists of a mandatory "1", "0" sequence for the first four most significant bits as shown. This is common to all the Serial EEPROM devices. the next one bit is fixed to zero and the next 2 bits being for memory page addressing. These page addressing bits on the 8K devices should be considered the most significant bits of the data word address which follows.

The eighth bit of the device address is the read/write operation select bit. A read operation is initiated if this bit is high and a write operation is initiated if this bit is low.

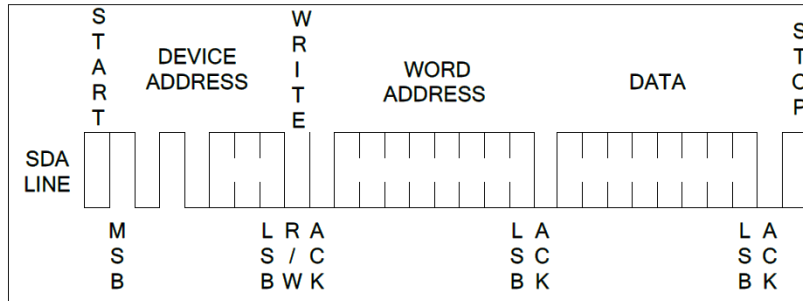
Upon a compare of the device address, the EEPROM will output a "0". If a compare is not made, the chip will return to a standby state.

4. Write Operations

BYTE WRITE: A write operation requires an 8-bit data word address following the device address word and acknowledgment. Upon receipt of this address, the EEPROM will again respond with a "0" and then clock in the first 8-bit data word. Following receipt of the 8-bit data word, the EEPROM will output a "0" and the addressing device, such as a microcontroller, must terminate the write sequence with a stop condition. At this time the EEPROM enters an internally timed write cycle, t_{WR} , to the nonvolatile memory. All inputs are disabled during this write cycle and the EEPROM will not respond until the write is complete (see Figure 5).

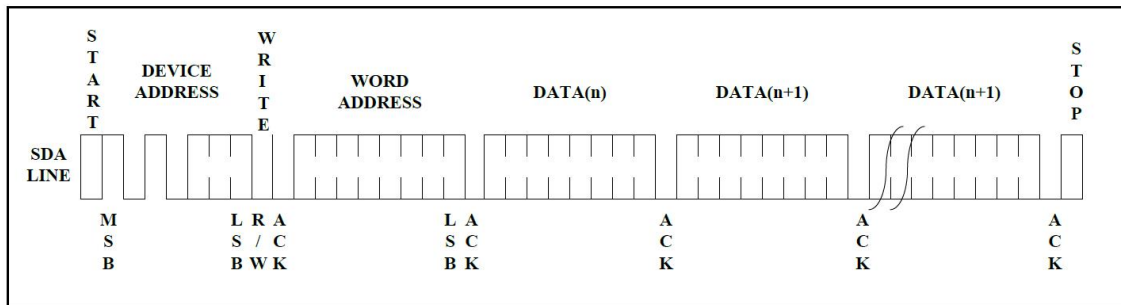


Figure 5 Byte Write



PAGE WRITE: A page write is initiated the same as a byte write, but the microcontroller does not send a stop condition after the first data word is clocked in. Instead, after the EEPROM acknowledges receipt of the first data word, the microcontroller can transmit up to fifteen more data words. The EEPROM will respond with a "0" after each data word received. The microcontroller must terminate the page write sequence with a stop condition (see Figure 6).

Figure 6 Page Write



The data word address lower four bits are internally incremented following the receipt of each data word. The higher data word address bits are not incremented, retaining the memory page row location. When the word address, internally generated, reaches the page boundary, the following byte is placed at the beginning of the same page. If more than sixteen data words are transmitted to the EEPROM, the data word address will "roll over" and previous data will be overwritten.

ACKNOWLEDGE POLLING: Once the internally timed write cycle has started and the EEPROM inputs are disabled, acknowledge polling can be initiated. This involves sending a start condition followed by the device address word. The read/write bit is representative of the operation desired. Only if the internal write cycle has completed will the EEPROM respond with a "0", allowing the read or write sequence to continue.

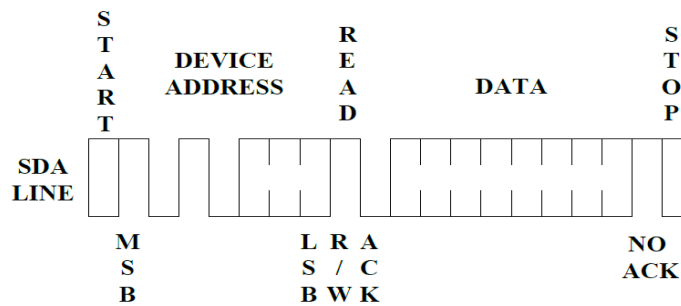


5. Read Operations

Read operations are initiated the same way as write operations with the exception that the read/write select bit in the device address word is set to "1". There are three read operations: current address read, random address read and sequential read.

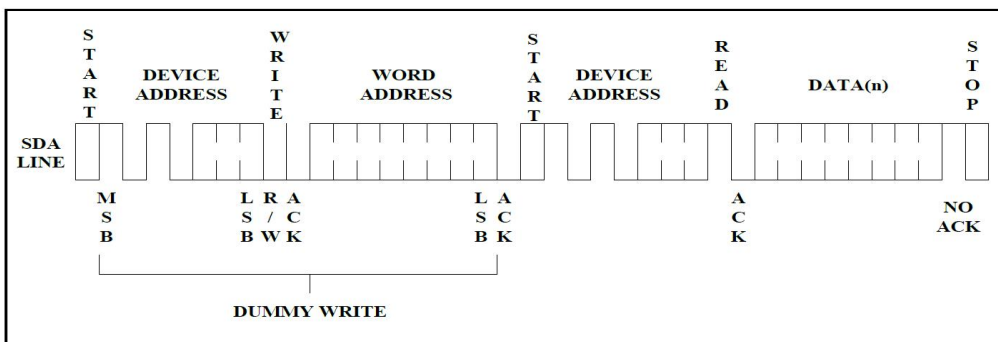
CURRENT ADDRESS READ: The internal data word address counter maintains the last address accessed during the last read or write operation, incremented by one. This address stays valid between operations as long as the chip power is maintained. The address "roll over" during read is from the last byte of the last memory page to the first byte of the first page. The address "roll over" during write is from the last byte of the current page to the first byte of the same page. Once the device address with the read/write select bit set to "1" is clocked in and acknowledged by the EEPROM, the current address data word is serially clocked out. The microcontroller does not respond with an input "0" but does generate a following stop condition (see Figure 7).

Figure 7 Current Address Read



RANDOM READ: A random read requires a "dummy" byte write sequence to load in the data word address. Once the device address word and data word address are clocked in and acknowledged by the EEPROM, the microcontroller must generate another start condition. The microcontroller now initiates a current address read by sending a device address with the read/write select bit high. The EEPROM acknowledges the device address and serially clocks out the data word. The microcontroller does not respond with a "0" but does generate a following stop condition (see Figure 8)

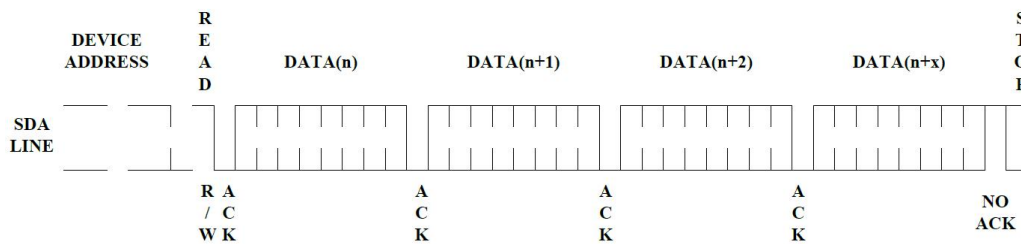
Figure 8 Random Read





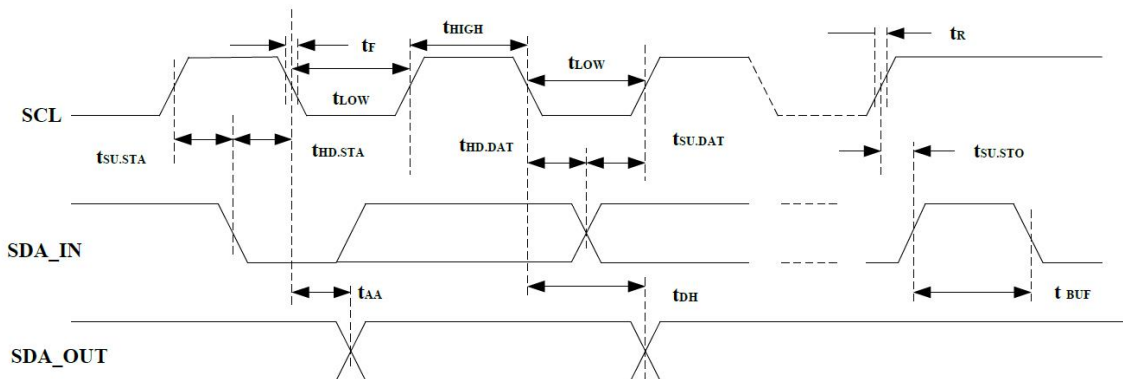
SEQUENTIAL READ: Sequential reads are initiated by either a current address read or a random address read. After the microcontroller receives a data word, it responds with an acknowledge. As long as the EEPROM receives an acknowledge, it will continue to increment the data word address and serially clock out sequential data words. When the memory address limit is reached, the data word address will "roll over" and the sequential read will continue. The sequential read operation is terminated when the microcontroller does not respond with a "0" but does generate a following stop condition (see Figure 9).

Figure 9 Sequential Read



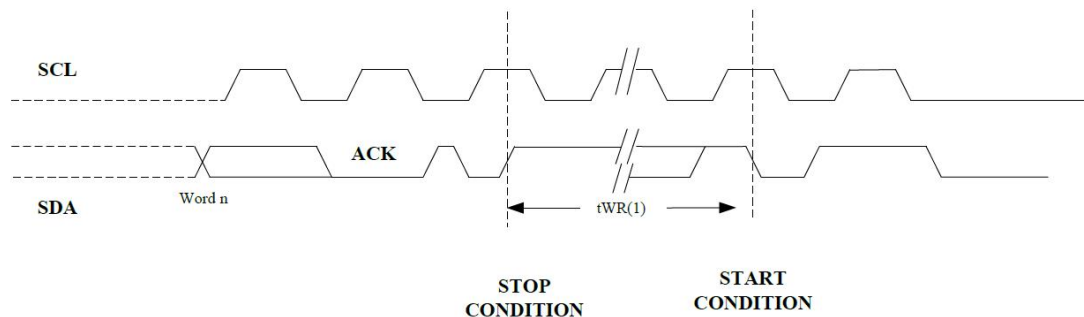
BUS TIMING

Figure 10 SCL: Serial Clock, SDA: Serial Data I/O



WRITE CYCLE TIMING

Figure 11 SCL: Serial Clock, SDA: Serial Data I/O

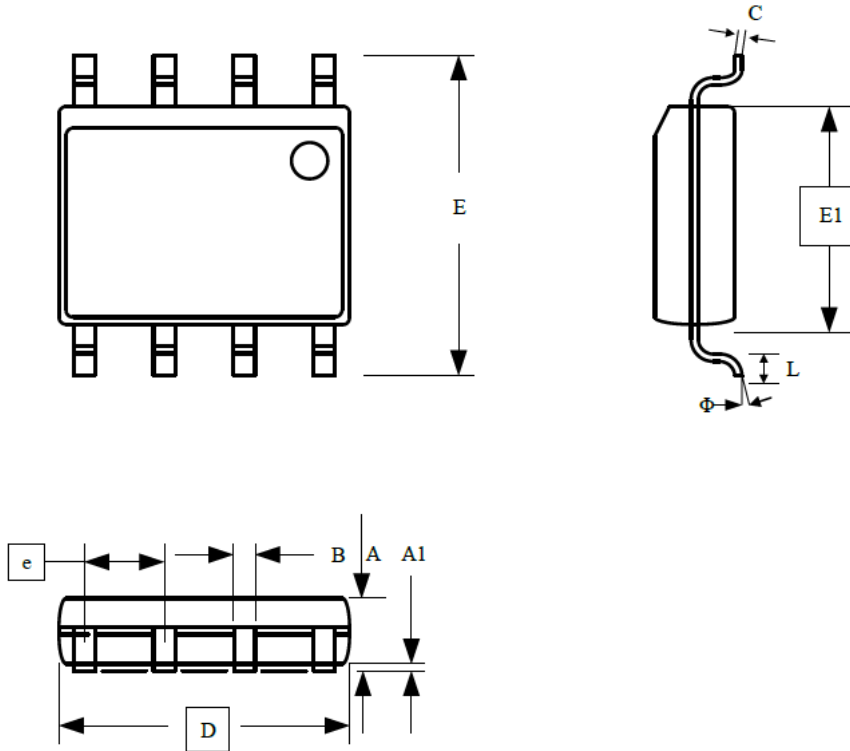


NOTE: The write cycle time t_{WR} is the time from a valid stop condition of a write sequence to the end of the internal clear/write cycle.



PACKAGE INFORMATION

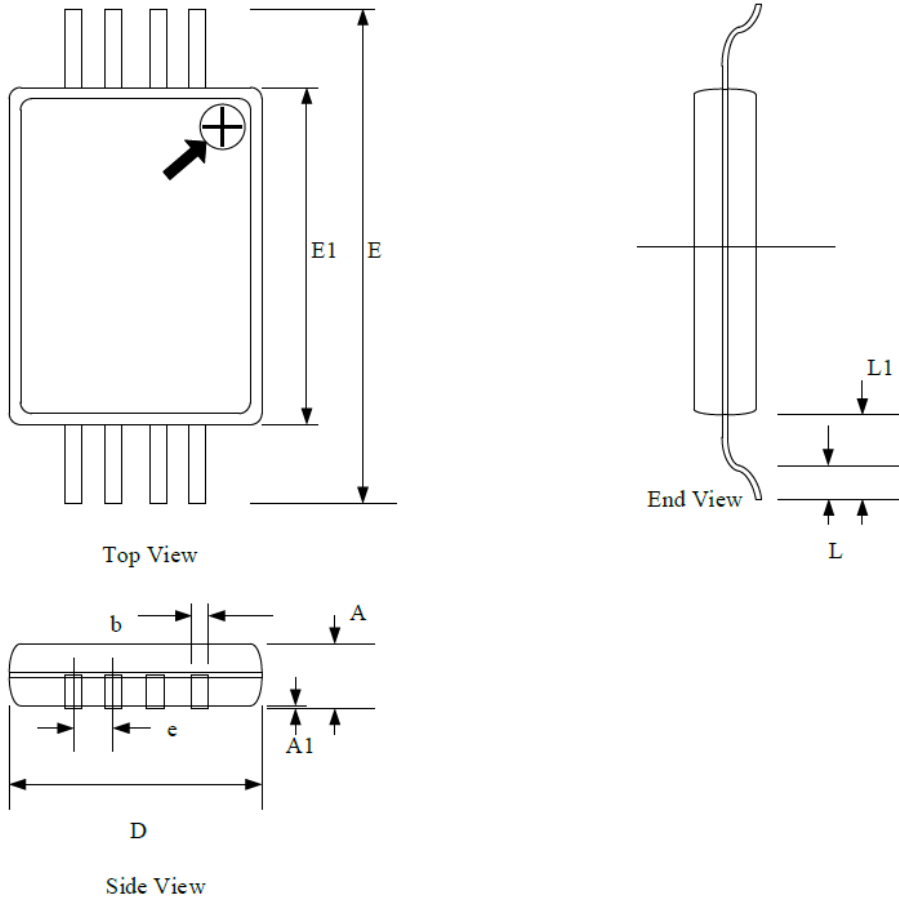
Dimension in SOP8 (Unit: mm)



Symbol	Min	Max
A	1.350	1.750
A1	0.100	0.230
B	0.390	0.480
C	0.210	0.260
D	4.700	5.100
E1	3.700	4.100
E	5.800	6.200
e	1.27BSC	
L	0.500	0.800
θ	0°	8°



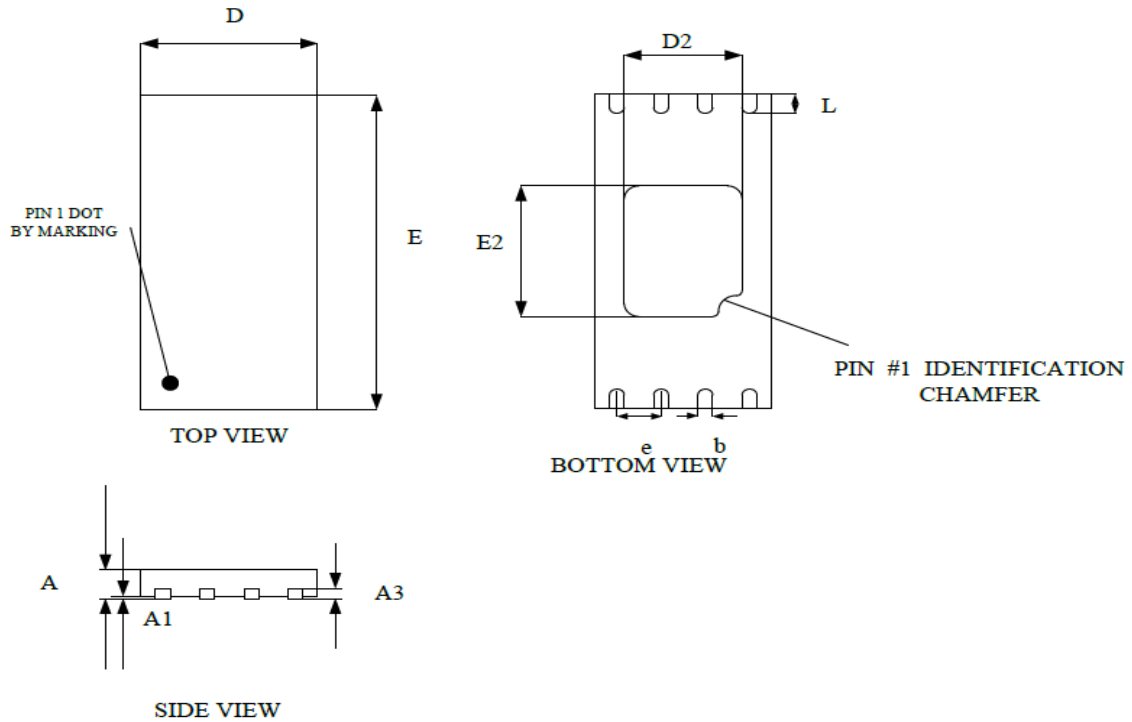
Dimension in TSSOP8 Package (Unit: mm)



Symbol	Min	Max
D	2.900	3.100
E	6.200	6.600
E1	4.300	4.500
A	-	1.200
A1	0.050	0.150
b	0.210	0.300
e	0.650 BSC	
L	0.450	0.750
L1	1.000 REF	



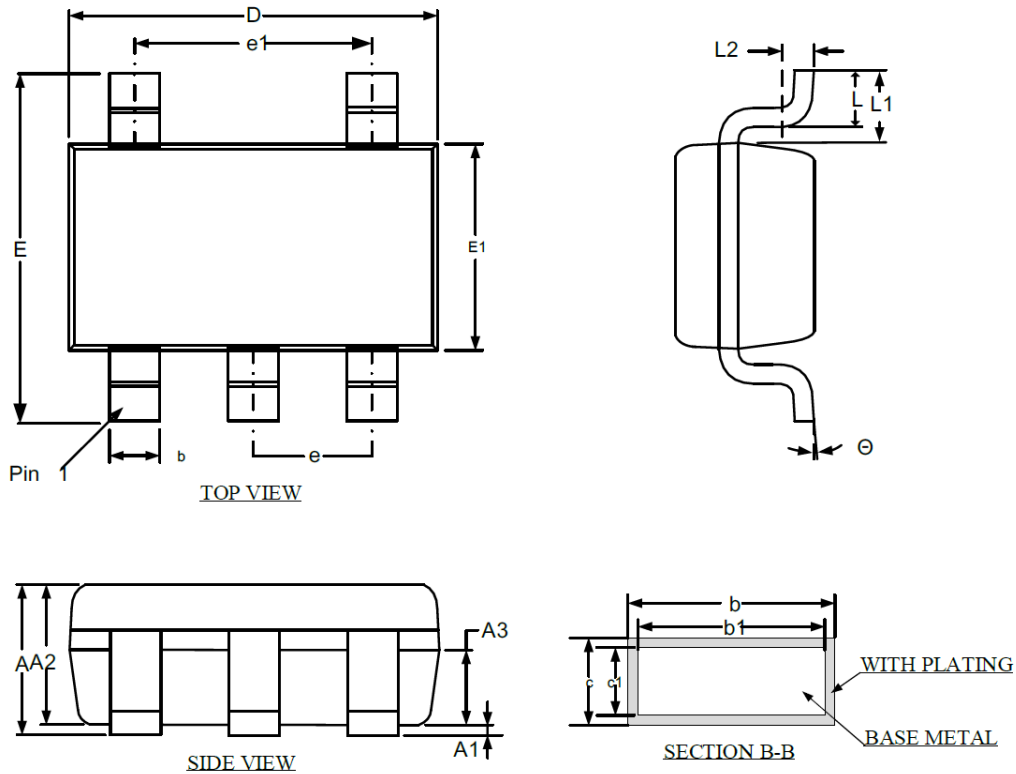
Dimension in DFN8 (Unit: mm)



Symbol	Min	Max
A	0.500	0.600
A1	0.000	0.050
A3	0.15 REF	
D	1.950	2.050
E	2.950	3.050
b	0.200	0.300
L	0.200	0.400
D2	1.250	1.500
E2	1.150	1.400
e	0.500 BSC	



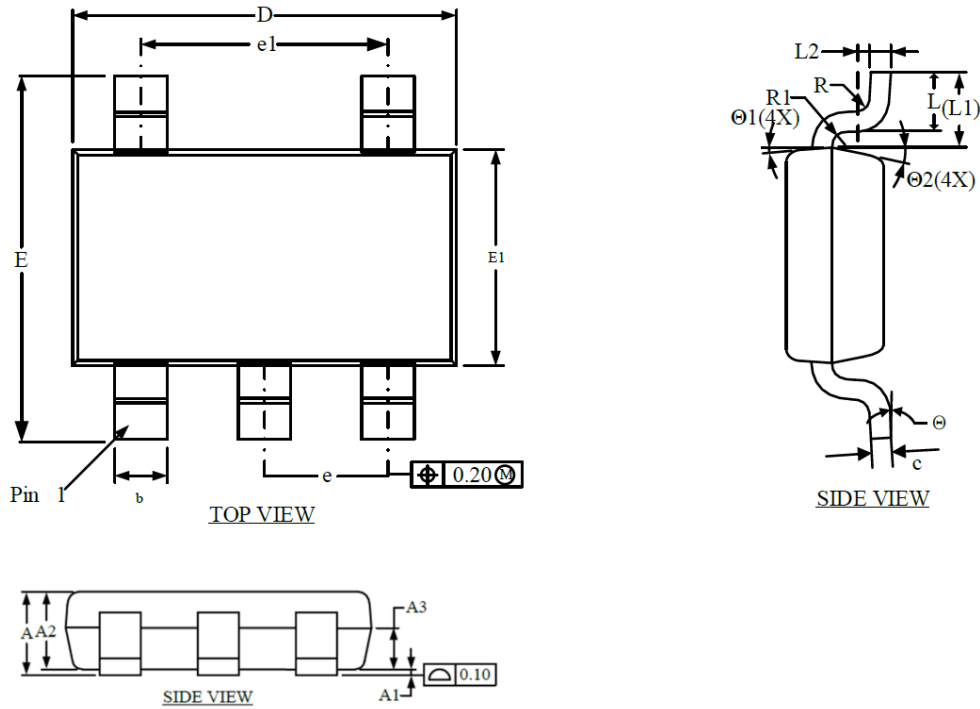
Dimension in SOT-25 (Unit: mm)



Symbol	Min.	Max.
A	-	1.350
A1	0.040	0.150
A2	1.000	1.200
A3	0.550	0.750
b	0.380	0.480
b1	0.370	0.430
c	0.110	0.210
c1	0.100	0.160
D	2.720	3.120
E	2.600	3.000
E1	1.400	1.800
e	0.950 BSC	
e1	1.900 BSC	
L	0.300	0.600
L1	0.575 REF	
L2	0.258 BSC	
θ	0°	8°



Dimension in TSOT-25 (Unit: mm)



Symbol	Min	Max
A	-	0.900
A1	0.000	0.100
A2	0.650	0.850
A3	0.350	0.450
b	0.300	0.500
c	0.140	0.200
D	2.850	3.050
E	2.650	2.950
E1	1.600	1.700
e	0.900	1.000
e1	1.800	2.000
L	0.300	0.600
L1	0.575 REF	
L2	0.258 BSC	
R	-	0.25
R1	-	0.25
θ	0°	8°
θ1	3°	7°
θ2	10°	14°



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